

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2N6260

DESCRIPTION

- With TO-66 package
- Low saturation voltage
- Wide safe operating area

APPLICATIONS

- Power switching circuits
- High-fidelity amplifiers
- Solenoid drivers
- Series and shunt-regulator driver and output stages

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

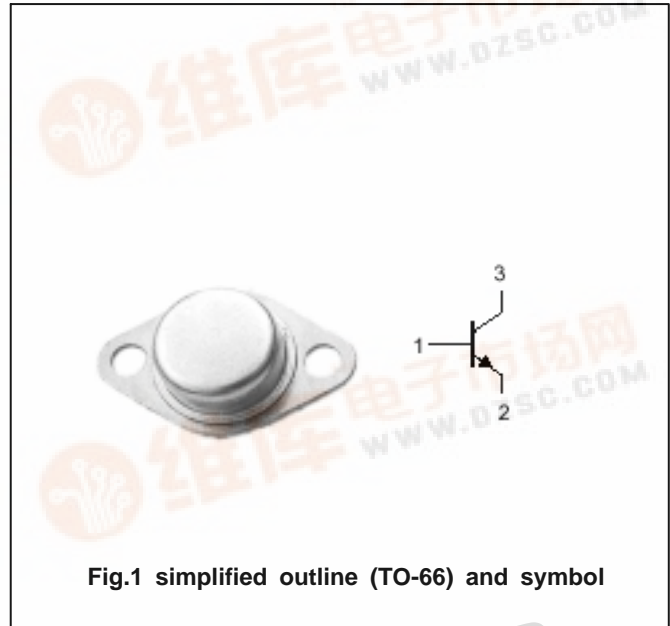


Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	50	V
V _{CEO}	Collector-emitter voltage	Open base	40	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		4	A
I _B	Base current		2	A
P _T	Total power dissipation	T _C =25	29	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-65~200	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance junction to case	3.5	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.1 A ; I _B =0	80			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =1.5A; I _B =0.15A			1.5	V
V _{BE}	Base -emitter on voltage	I _C =1.5A ; V _{CE} =2V			1.5	V
I _{CEV}	Collector cut-off current	V _{CE} =40V; V _{BE(off)} =-1.5V T _C =150			0.5 1.0	mA
I _{CEO}	Collector cut-off current	V _{CE} =30V; I _B =0			0.5	mA
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			0.2	mA
h _{FE-1}	DC current gain	I _C =4A ; V _{CE} =2V	5			
h _{FE-2}	DC current gain	I _C =1.5A ; V _{CE} =2V	20		100	

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PACKAGE OUTLINE

